# CSRI2×50-120

# SIC SCHOTTKY DIODE TYPE 2×50A

## **Features**

- High surge current capable
- Zero reverse recovery current VDC
- · High bandwidth
- Temperature Independent Switching Behavior 1200 V
- I<sub>F</sub> (Tc<135°C) 2×50 A
- Isolation type package

## **Benefits**

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices without thermal runaway

## **Applications**

- Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Power factor correction
- Diode snubber
- Automotive
- induction heating
- Welding equipment

# **Maximum Ratings**

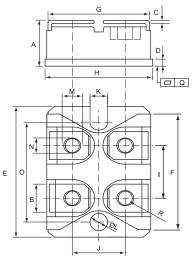
Operating Junction Temperature : - 55  $^{\circ}$ C to +175  $^{\circ}$ C

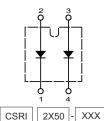
Storage Temperature :  $-55 \,^{\circ}\text{C}$  to  $+175 \,^{\circ}\text{C}$ 

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSRI2×50-120	1200V	1200V

Maximum Rating	Symbol	Conditions	Value	Unit		
		Tc=25°C, D=1		115		
Continuous forward current (per diode)	I <sub>F</sub>	Tc=100°C, D=1		76	А	
,		Tc=135°C, D=1		50		
Non-repetitive peak forward current		Tc=25°C, tp=10ms		400	А	
sine half wave (per diode)	I <sub>FSM</sub>	Tc=150°C, tp=10ms		320		
Repetitive peak forward current		Tc=25°C, tp=10ms		240	А	
sine half wave (per diode)	I <sub>FRM</sub>	Tc=150°C, tp=10ms		168		
Non-repetitive peak forward current (per diode)	I <sub>F,max</sub>	Tc=25°C, tp=10μs		2000	Α	
Repetitive peak reverse voltage	$V_{RRM}$	Tj=25°C		1200	٧	
I <sup>2</sup> t value (per diode)	∫i <sup>2</sup> dt	Tc=25°C, tp=10ms		800	A <sup>2</sup> s	
Diode dv/dt ruggedness (per diode)	dv/dt	V <sub>R</sub> = 0~960V		200	V/ns	
Power dissipation (per diode)	P <sub>tot</sub>	Tc=25°C		405	W	
la eletion veltano	Viso	50/60Hz, RMS	t=1s	3000	V	
Isolation voltage	VISO	I <sub>ISOL</sub> ≤1 mA	t=60s	2500		
Mounting torque		To heatsink		1.5	Nm	
Mounting torque		To terminal		1.3	INIII	







DIMENSIONS						
	INCH	HES	М	М		
	MIN	MAX	MAX MIN			
Α	0.460	0.483	11.68	12.28		
В	0.307	0.323	7.80	8.20		
С	0.030	0.033	0.75	0.85		
D	0.071	0.081	1.80	2.05		
Е	1.488	1.504	37.80	38.20		
F	1.248	1.260	31.70	32.00		
G	0.917	0.957	23.30	24.30		
Н	0.996	1.008	25.30	25.60		
I	0.579	0.602	14.70	15.30		
J	0.492	0.516	12.50	13.10		
K	0.161	0.169	4.10	4.30		
L	0.161	0.169	4.10	4.30		
М	0.181	0.197	4.60	5.00		
N	0.165	0.181	4.20	4.60		
0	1.181	1.197	30.00	30.40		
Q	-0.002	0.004	-0.05	0.10		
R	M//*Q					

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## Electrical Characteristics, at T<sub>i</sub>=25 °C, unless otherwise specified. (per diode)

Static Characteristics	Comple ed	Conditions	Values			
	Symbol	Conditions	min.	typ.	max.	Unit
DC blocking voltage	V <sub>DC</sub>		1,200	-	-	V
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> =50A, T <sub>j</sub> =25 °C	-	1.6	1.8	V
		I <sub>F</sub> =50A, T <sub>j</sub> =175 °C	-	2.4	2.9	
Reverse current	I <sub>R</sub>	V <sub>R</sub> =1,200V, T <sub>j</sub> =25 °C	-	5	25	μ <b>Α</b>
		V <sub>R</sub> =1,200V, T <sub>j</sub> =175 °C	-	50	250	

## AC Characteristics (per diode)

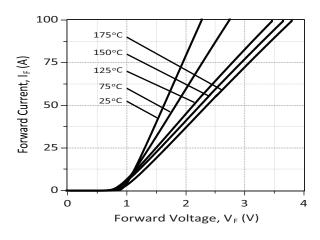
Static Characteristics	Combal	Conditions	Values			
	Symbol	Conditions	min.	typ.	max.	Unit
Total capacitive charge	Q <sub>C</sub>	di/dt =1000A/µs IF = 50A, VR =600V	-	93.2	-	nC
Switching time	t <sub>s</sub>		-	19.2	-	ns
Total capacitance		V <sub>R</sub> =1V, f=1 MHz T <sub>j</sub> =25 °C	-	2,042	-	
	С	V <sub>R</sub> =400V, f=1 MHz T <sub>j</sub> =25 °C	-	185	-	pF
		V <sub>R</sub> =800V, f=1 MHz T <sub>j</sub> =25 °C	-	160	-	

## Thermal Characteristics (per diode)

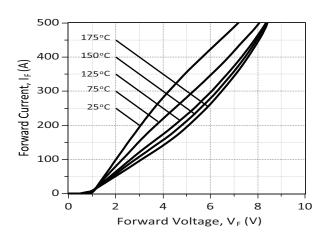
Chatia Chamantaniatian	Comple ed	Values	Unit	
Static Characteristics	Symbol	typ.		
Thermal resistance from junction to case	$R_{ heta JC}$	0.37	°C/W	

#### **Typical Performance**

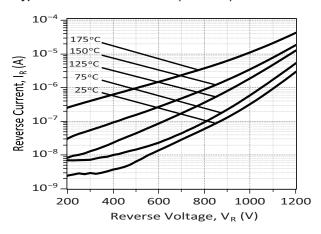
#### Typical Forward Characteristics (Per diode)



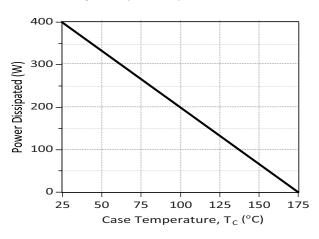
#### Typical High Current Forward Characteristics (Per diode)



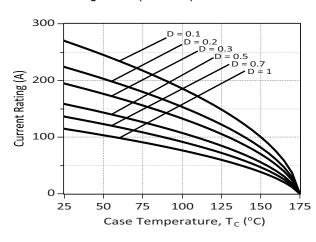
#### Typical Reverse Characteristics (Per diode)



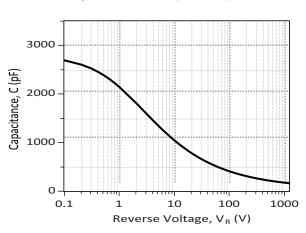
Power Derating Curve (Per diode)



#### **Current Derating Curves (Per diode)**



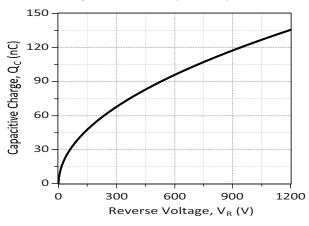
Typical Junction Capacitance vs.
Reverse Voltage Characteristics (Per diode)



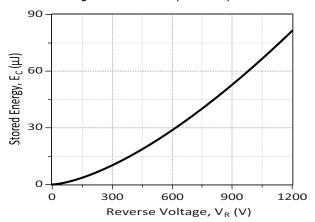


#### **Typical Performance**

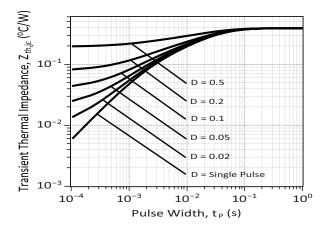
#### Typical Capacitive Charge vs. Reverse Voltage Characteristics (Per diode)



# Typical Capacitive Energy vs. Reverse Voltage Characteristics (Per diode)



#### Transient Thermal Impedance (Per diode)



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